REMARKS

This application has been carefully reviewed in light of the Office Action dated September 15, 2003. Claims 1-11 remain pending in this application. Claim 1 is the independent claim. Favorable reconsideration is respectfully requested.

In response to the Office Action's objections the specification, Applicants respectfully believe the amendments to the specification adequately respond to the objection and render it moot. Applicants request withdrawal of the objection to the specification.

On the merits, the Office Action rejected Claims 1-11 under 35 U.S.C. § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Applicants respectfully submit that the amendments to Claim 1 adequately respond to the § 112, second paragraph rejection and request its withdrawal.

Further on the merits, the Office Action rejected Claims 1-11 under 35 U.S.C. § 102(b) as being anticipated by Kanda et al. (U.S. Patent No. 5,204,274; hereinafter "Kanda"). Applicants respectfully believe Claim 1 to be allowable for at least the following reasons:

Applicants' Claim 1 recites, in pertinent part: "A method of manufacturing a semiconductor device... in a stage after the first semiconductor layer has been removed at the location of the intermediate region and before the second semiconductor layer is deposited, strips of an electrically insulating material separating the emitter region from the isolation region are formed at two opposite sides of the active region at the location where the intermediate region between the base contact and the collector contact is adjacent to the isolation region."

Kanda fails to recite or suggest forming additional strips of electrically insulating material at the edge of the active region in the intermediate region where the emitter will be formed. Fig. 2H of Kanda shows the active region in the silicon body circumferentially surrounded with a pattern of silicon oxide recessed in the body. The emitter in the transistor obtained in this way adjoins the recessed silicon oxide on three sides at the circumference of the active region. Thus Kanda fails to recite or suggest providing the emitter in the center of the active region at some distance from the edges of the active region. Thus a device formed by the method of Kanda will have higher leakage between the base and collector than a device formed by the method of Applicants' Claim 1. Claim 1 is believed patentable over Kanda for at least these reasons.

Claims 2-11 depend from independent Claim 1 discussed above and are believed patentable for at least the same reasons. In addition, Applicants respectfully believe Claims 2-11 to be independently patentable and request separate consideration of each claim.

In view of the foregoing remarks, Applicants respectfully request favorable reconsideration and early passage to issue of the present application.

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Respectfully submitted,

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